

30 V, dual N-channel Trench MOSFET 25 March 2015

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Exposed drain pad for excellent thermal conduction

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	590	mA
Static characteristics (per transistor)						,	
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 590 mA; T _j = 25 °C		-	550	670	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa256
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

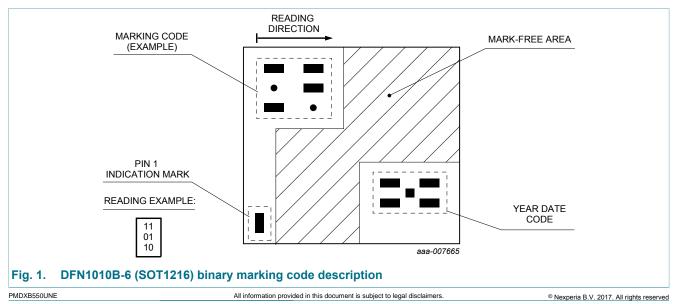
6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMDXB550UNE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

7. Marking

Table 4.Marking codes

Type number	Marking code
PMDXB550UNE	01 10 00



8. Limiting values

Table 5.Limiting values

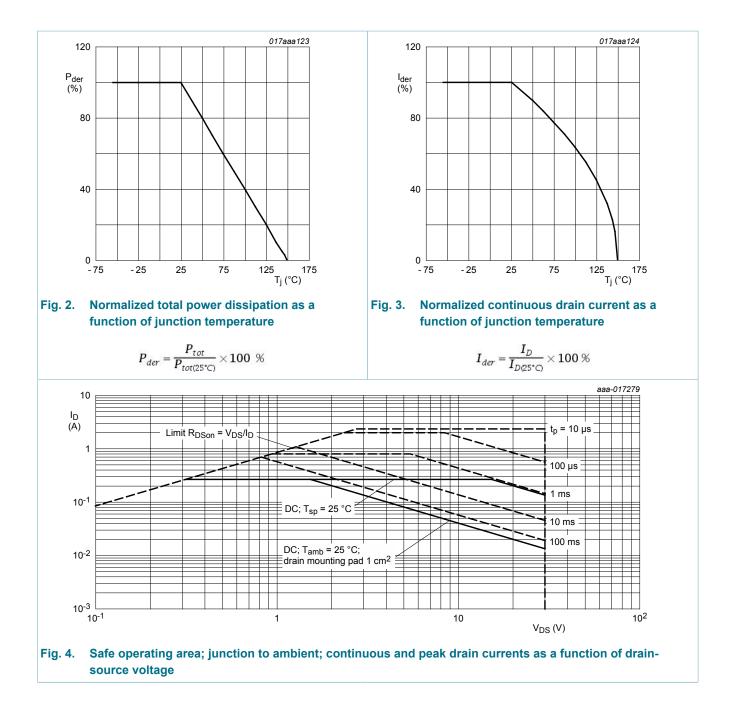
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	590	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	370	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	2.3	А
P _{tot} total power d	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	410	mW
		T _{sp} = 25 °C		-	4030	mW
Source-dra	in diode		1			
l _S	source current	T _{amb} = 25 °C		-	380	mA
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	R _{th(j-a)} thermal resistance	in free air	[1]	-	380	440	K/W
	from junction to ambient		[2]	-	275	305	K/W

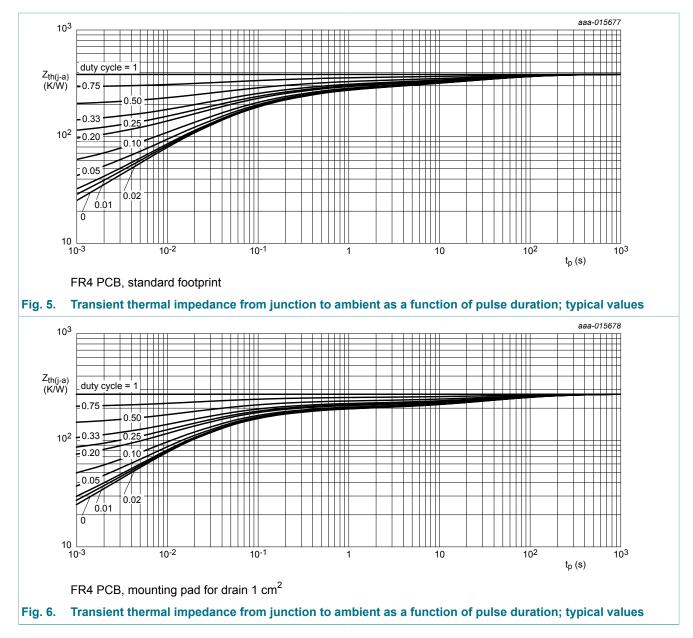
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



10. Characteristics

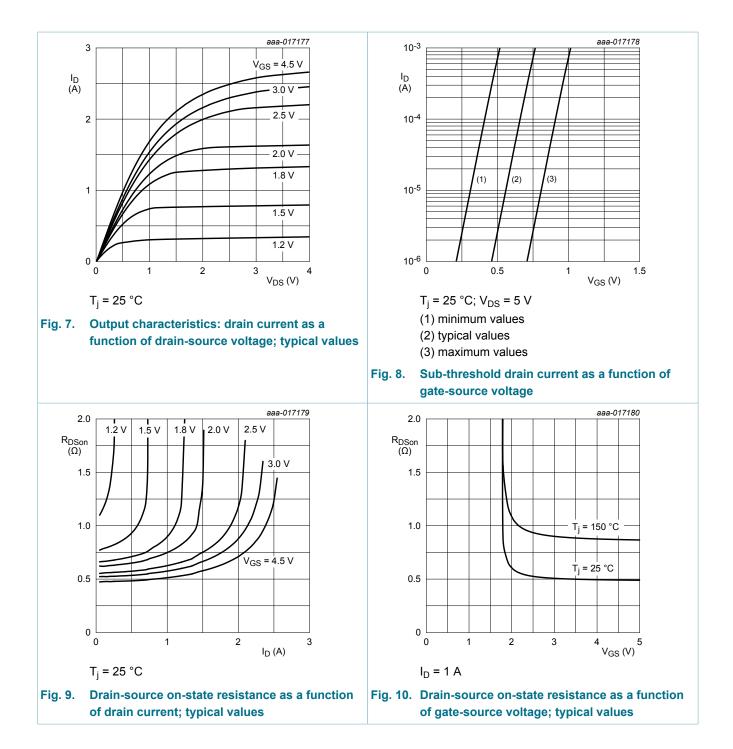
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics (per transistor)	· · · · ·	I			
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	0.45	0.7	0.95	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon} drain-source of resistance	drain-source on-state	V_{GS} = 4.5 V; I _D = 590 mA; T _j = 25 °C	-	550	670	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 590 mA; T _j = 150 °C	-	960	1170	mΩ
		V _{GS} = 2.5 V; I _D = 590 mA; T _j = 25 °C	-	660	900	mΩ
		V _{GS} = 1.8 V; I _D = 80 mA; T _j = 25 °C	-	770	1120	mΩ
		V _{GS} = 1.5 V; I _D = 10 mA; T _j = 25 °C	-	890	1500	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 590 mA; T _j = 25 °C	-	600	-	mS
Dynamic ch	aracteristics (per transist	or)	I			
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 590 mA; V _{GS} = 4.5 V;	-	0.6	1.05	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	30.3	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.8	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I _D = 590 mA; V _{GS} = 4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
t _{d(off)}	turn-off delay time	1	-	12	-	ns
t _f	fall time	1	-	3	-	ns
Source-drai	n diode (per transistor)					
V _{SD}	source-drain voltage	I _S = 380 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.86	1.2	V

PMDXB550UNE

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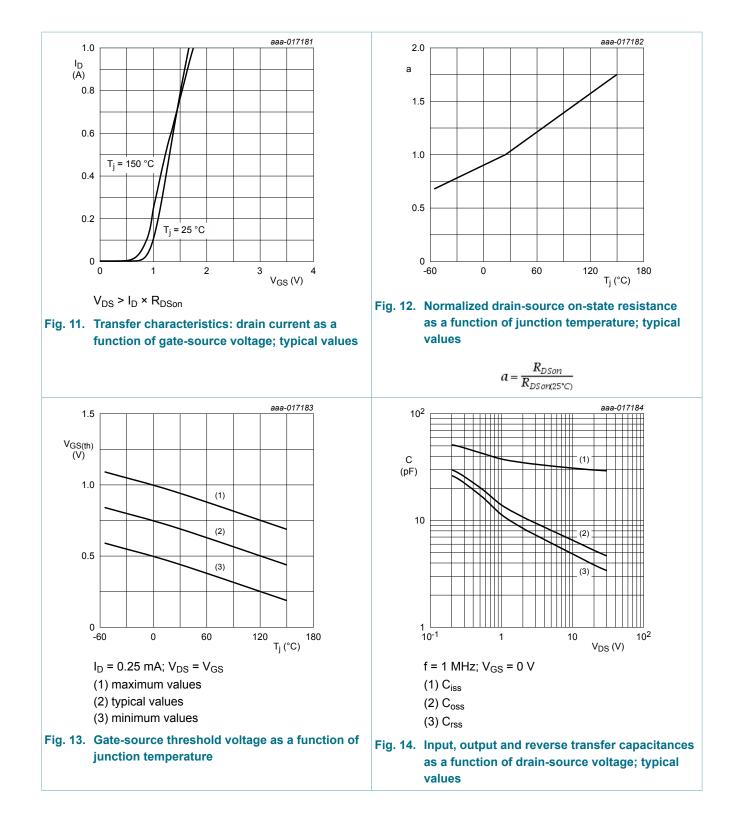
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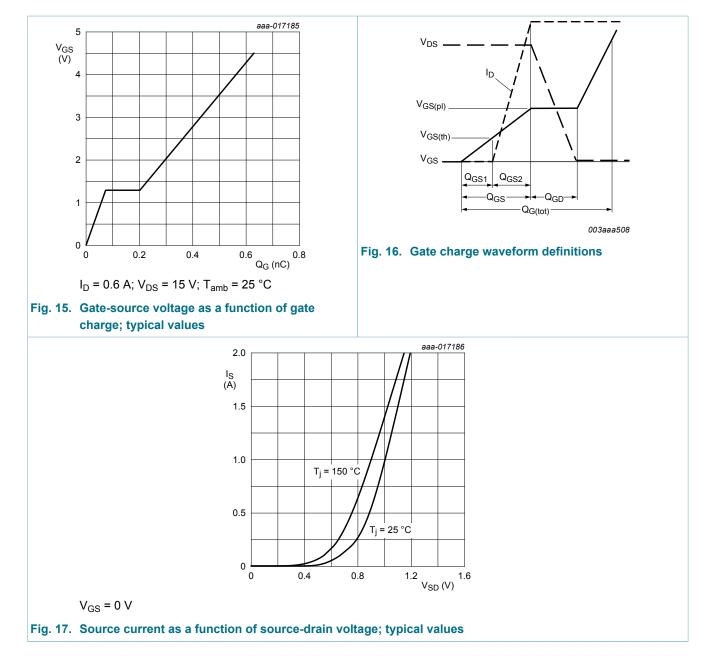
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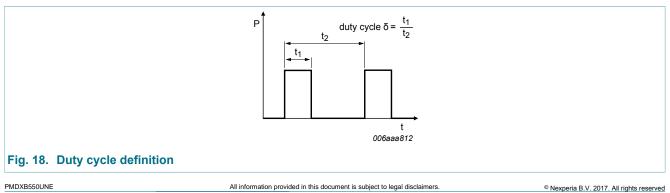
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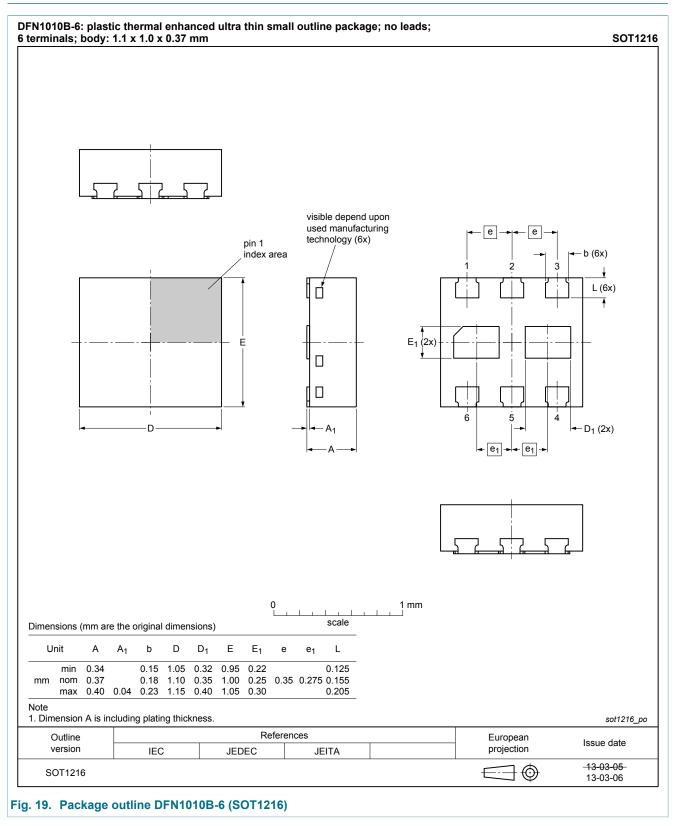


11. Test information



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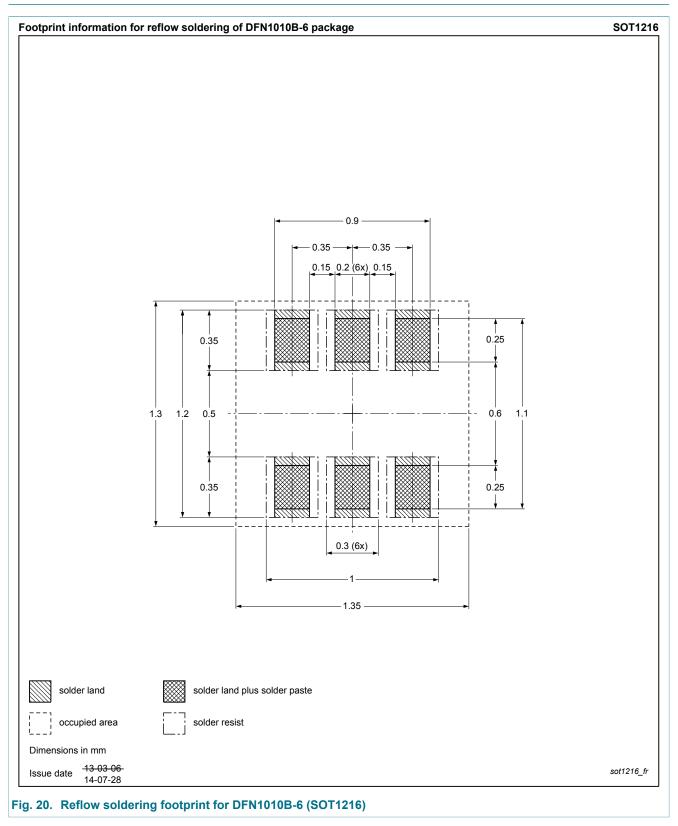
12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision his	ble 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMDXB550UNE v.1	20150325	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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